Alfa-MOS Technology

AFC3326WS
30V N & P Pair Enhancement Mode MOSFET

General Description

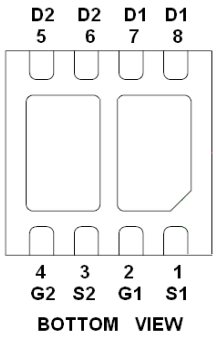
AFC3326WS, N & P Pair enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent RDS(ON), low gate charge.
These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

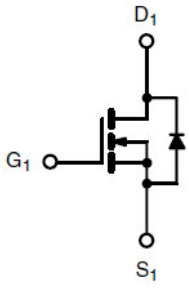
Features

N-Channel
- 30V/12A,$R_{DS(ON)}$=36mΩ@V_{GS}=10V
- 30V/10A,$R_{DS(ON)}$=46mΩ@V_{GS}=4.5V

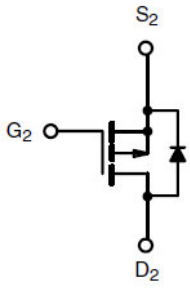
P-Channel
- -30V/-8A,$R_{DS(ON)}$=60mΩ@V_{GS}=10V
- -30V/-6A,$R_{DS(ON)}$=80mΩ@V_{GS}=4.5V

Pin Description (DFN3X3-8L)

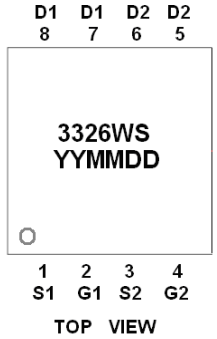




N-Channel MOSFET



P-Channel MOSFET



Application

- DC/DC Conversion
- Load Switch
- DC FAN

Pin Define

Pin	Symbol	Description
1	S1	Source 1
2	G1	Gate 1
3	S2	Source 2
4	G2	Gate 2
5	D2	Drain 2
6	D2	Drain 2
7	D1	Drain 1
8	D1	Drain 1

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFC3326WSFN338RG	3326WS YYMMDD	DFN3X3-8L	Tape & Reel	5000 EA

※ YY year code
※ MM month code
※ DD date code
※ AFC3326WSFN338RG : 13” Tape & Reel ; Pb- Free ; Halogen- Free

Absolute Maximum Ratings (N-Channel)

(T_A=25℃ Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	30	V
Gate –Source Voltage		V_{GSS}	±20	V
Continuous Drain Current(T_J=150℃)	T_A=25℃	I_D	12	A
	T_A=70℃		10	
Pulsed Drain Current		I_{DM}	50	A
Continuous Source Current(Diode Conduction)		I_S	10	A
Power Dissipation	T_A=25℃	P_D	2	W
	T_A=70℃		1.5	
Operating Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	56	℃/W

Electrical Characteristics (N-Channel)

(T_A=25℃ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	1.3		2.1	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=24V,V_{GS}=0V			1	uA
		V_{DS}=24V,V_{GS}=0V T_J=85℃			30	
On-State Drain Current	$I_{D(on)}$	V_{DS}≧5V,V_{GS}=4.5V	10			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=12A		30	36	mΩ
		V_{GS}=4.5V,I_D=10A		40	46	
Forward Transconductance	g_{FS}	V_{DS}=15V,I_D=5.2A		13		S
Diode Forward Voltage	V_{SD}	I_S=1.6A,V_{GS}=0V		0.8	1.3	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=20V,V_{GS}=4.5V I_D≡5.2A		8	12	nC
Gate-Source Charge	Q_{gs}			1.6		
Gate-Drain Charge	Q_{gd}			2.4		
Input Capacitance	C_{iss}	V_{DS}=20V,V_{GS}=0V f=1MHz		700		pF
Output Capacitance	C_{oss}			75		
Reverse Transfer Capacitance	C_{rss}			45		
Turn-On Time	$t_{d(on)}$	V_{DD}=15V,R_L=15Ω I_D≡1.0A,V_{GEN}=10V R_G=6Ω		8	12	ns
	t_r			12	18	
Turn-Off Time	$t_{d(off)}$			28	40	
	t_f			10	18	

Absolute Maximum Ratings (P-Channel)

(T_A=25℃ Unless otherwise noted)

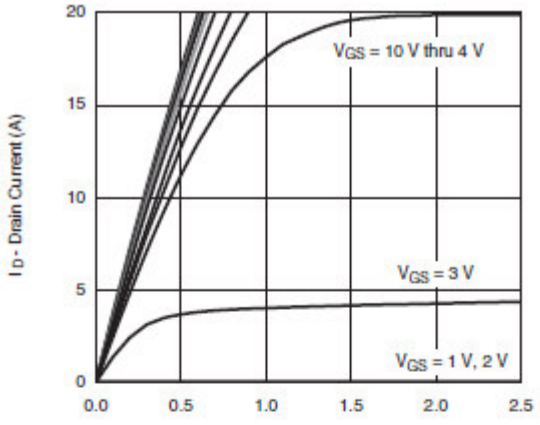
Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	-30	V
Gate –Source Voltage		V_{GSS}	±20	V
Continuous Drain Current(TJ=150℃)	T_A=25℃	I_D	-8.0	A
	T_A=70℃		-6.0	
Pulsed Drain Current		I_{DM}	-30	A
Continuous Source Current(Diode Conduction)		I_S	-10	A
Power Dissipation	T_A=25℃	P_D	1.8	W
	T_A=70℃		1.2	
Operating Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	62.5	℃/W

Electrical Characteristics (P-Channel)

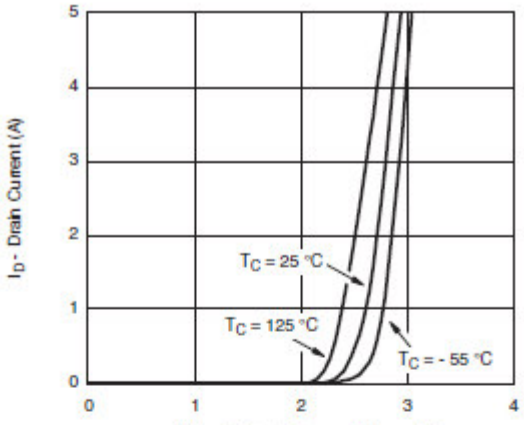
(T_A=25℃ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=-250uA	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250uA	-1.0		-2.0	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-24V,V_{GS}=0V			1	uA
		V_{DS}=-24V,V_{GS}=0V T_J=85℃			-30	
On-State Drain Current	$I_{D(on)}$	V_{DS}≧-5V,V_{GS}=-10V	25			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V,I_D=-8A		50	60	mΩ
		V_{GS}=-4.5V,I_D=-6A		70	80	
Forward Transconductance	g_{FS}	V_{DS}=-10V,I_D=-4.9A		10		S
Diode Forward Voltage	V_{SD}	I_S=-1.7A,V_{GS}=0V		0.8	1.3	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=-15V,V_{GS}=-10V I_D≡-5.0A		10	18	nC
Gate-Source Charge	Q_{gs}			1.6		
Gate-Drain Charge	Q_{gd}			3.0		
Input Capacitance	C_{iss}	V_{DS}=-15V,V_{GS}=0V f=1MHz		500		pF
Output Capacitance	C_{oss}			100		
Reverse Transfer Capacitance	C_{rss}			55		
Turn-On Time	$t_{d(on)}$	V_{DD}=-15V,R_L=15Ω I_D≡-1.0A,V_{GEN}=10V R_G=6Ω		8	18	ns
	t_r			8	18	
Turn-Off Time	$t_{d(off)}$			25	50	
	t_f			25	35	

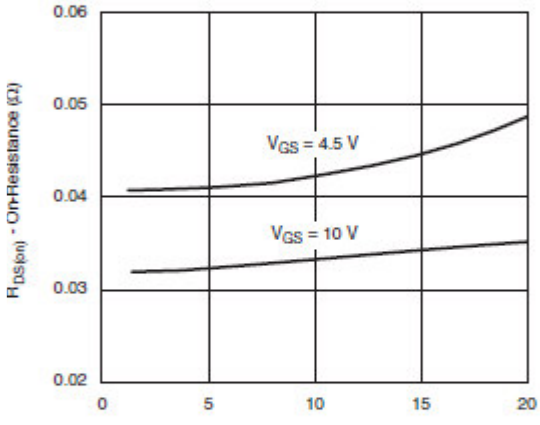
Typical Characteristics (N-Channel)



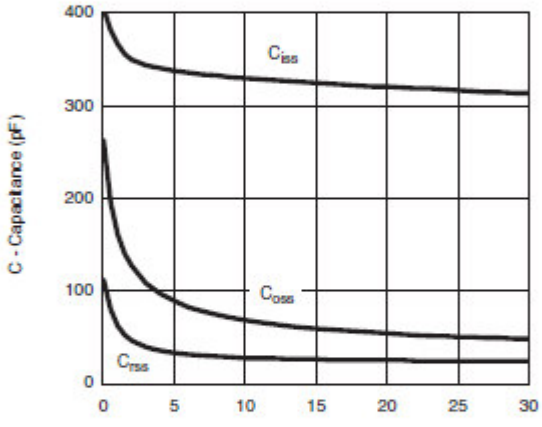
Output Characteristics



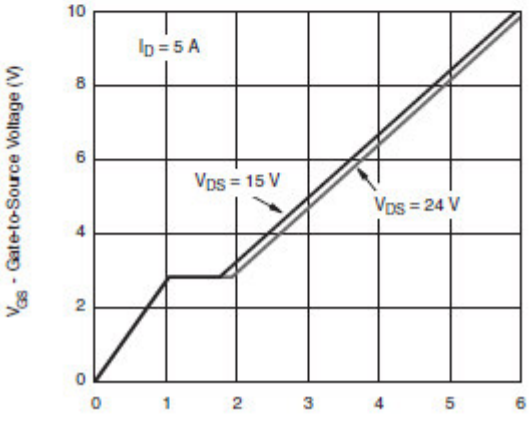
Transfer Characteristics



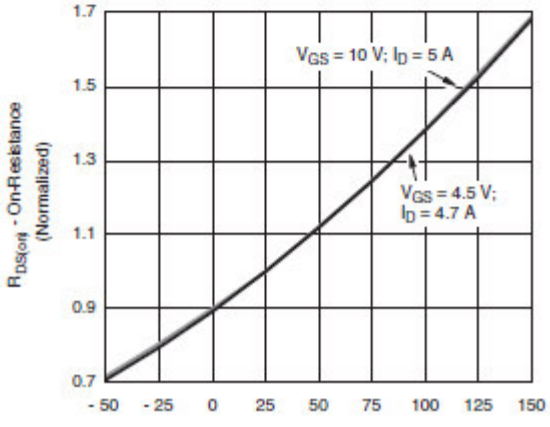
On-Resistance vs. Drain Current



Capacitance

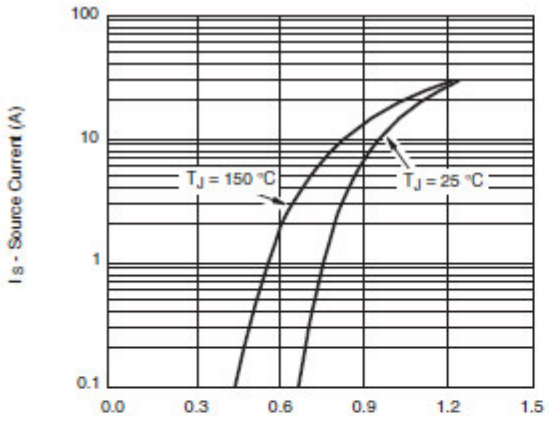


Gate Charge

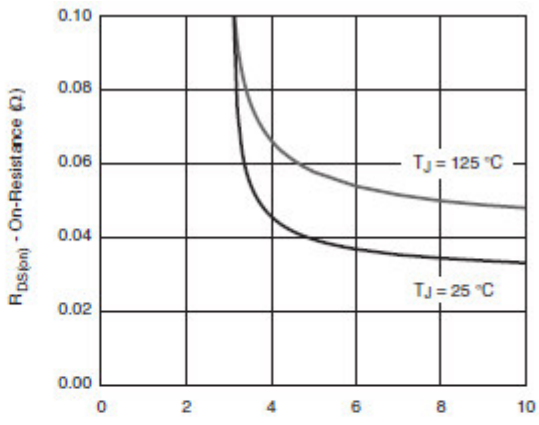


On-Resistance vs. Junction Temperature

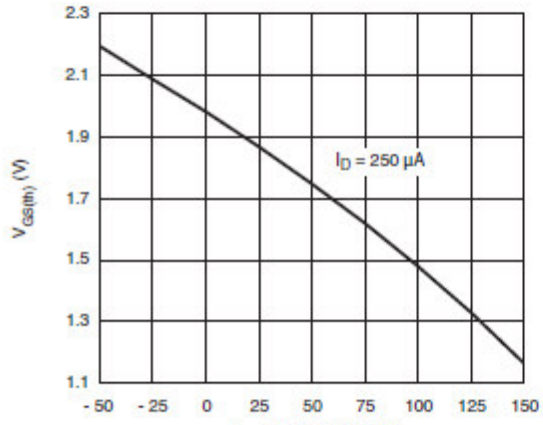
Typical Characteristics (N-Channel)



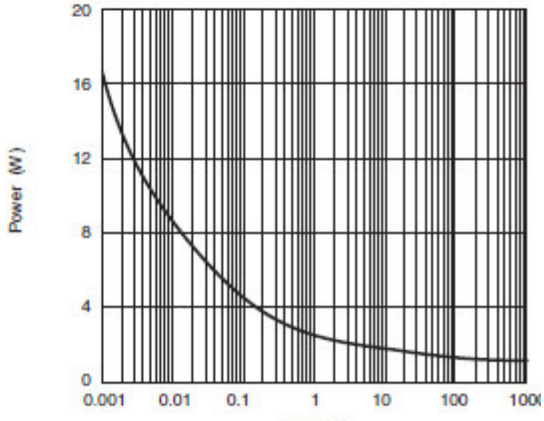
Source-Drain Diode Forward Voltage



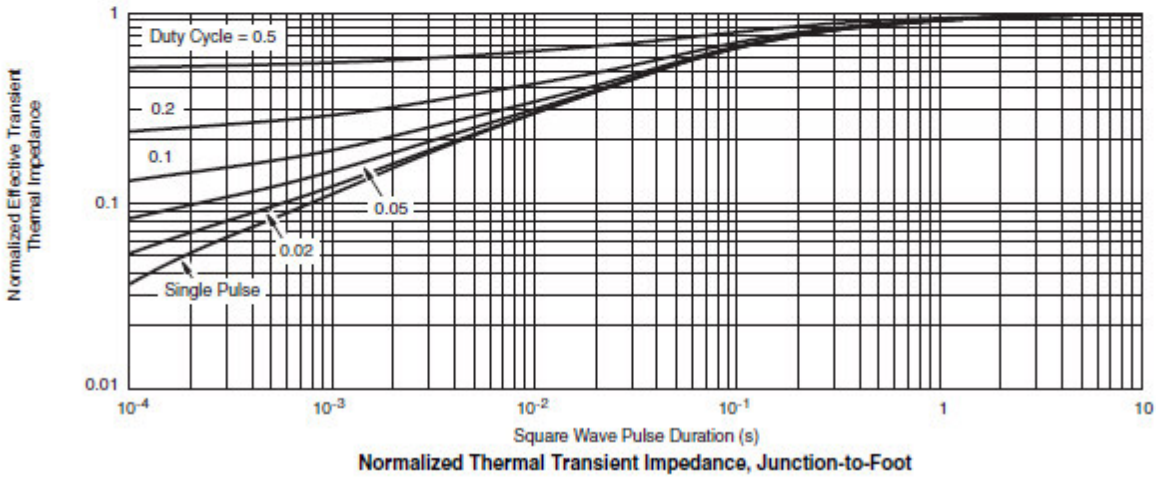
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



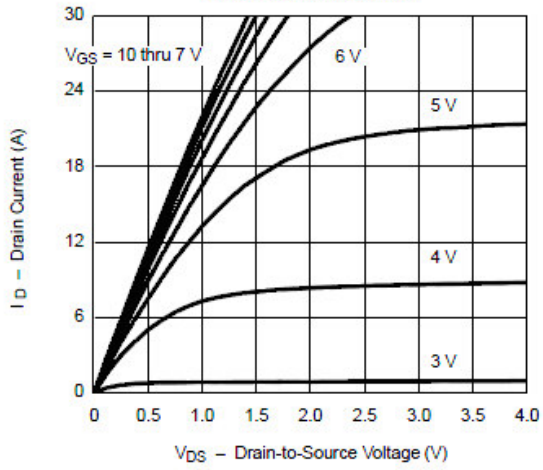
Single Pulse Power



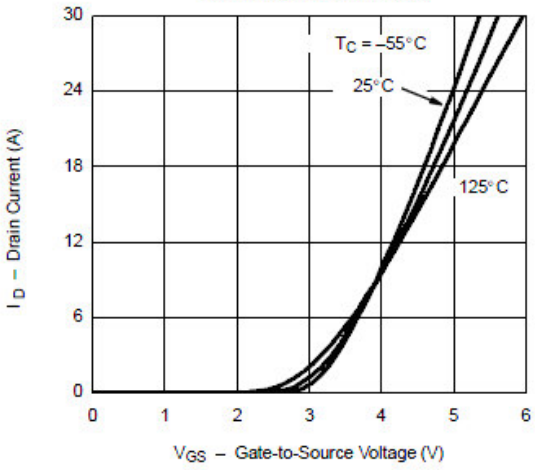
Normalized Thermal Transient Impedance, Junction-to-Foot

Typical Characteristics (P-Channel)

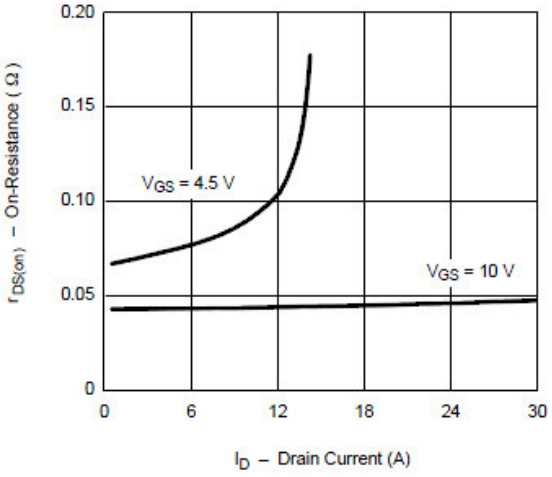
Output Characteristics



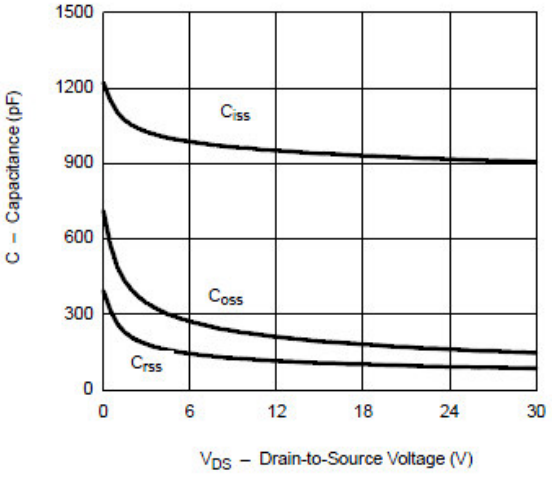
Transfer Characteristics



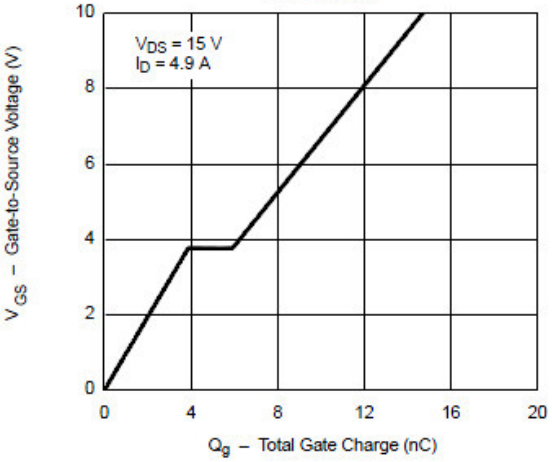
On-Resistance vs. Drain Current



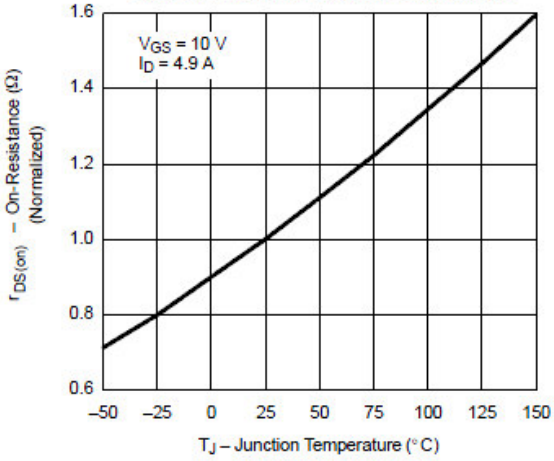
Capacitance



Gate Charge

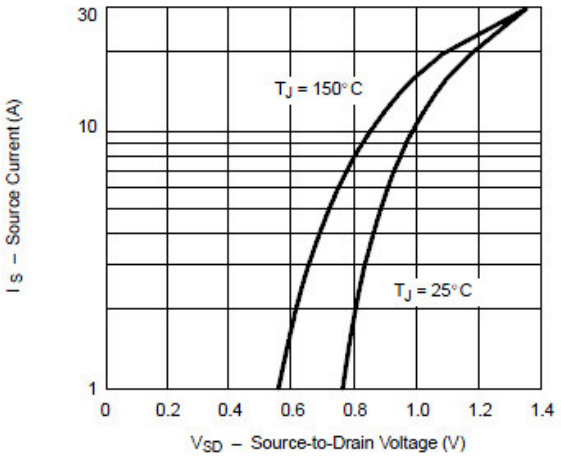


On-Resistance vs. Junction Temperature

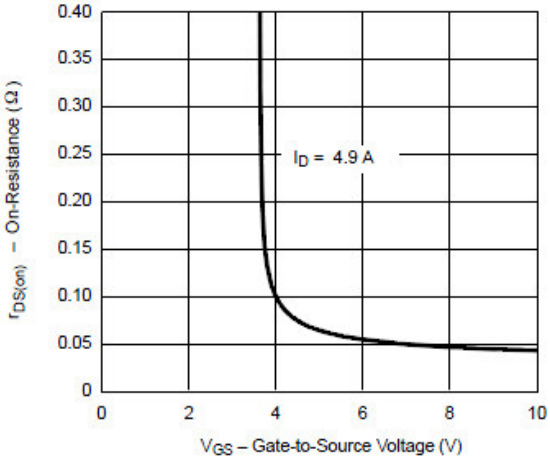


Typical Characteristics (P-Channel)

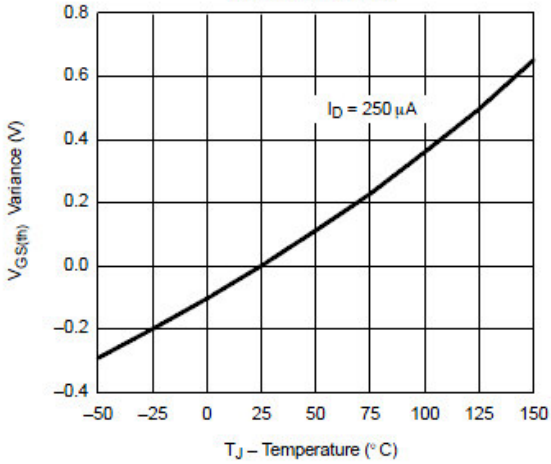
Source-Drain Diode Forward Voltage



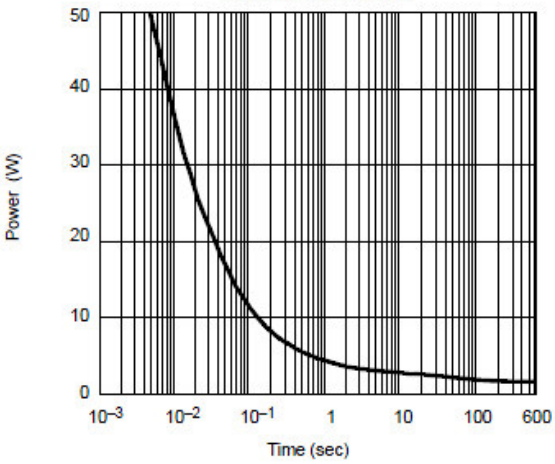
On-Resistance vs. Gate-to-Source Voltage



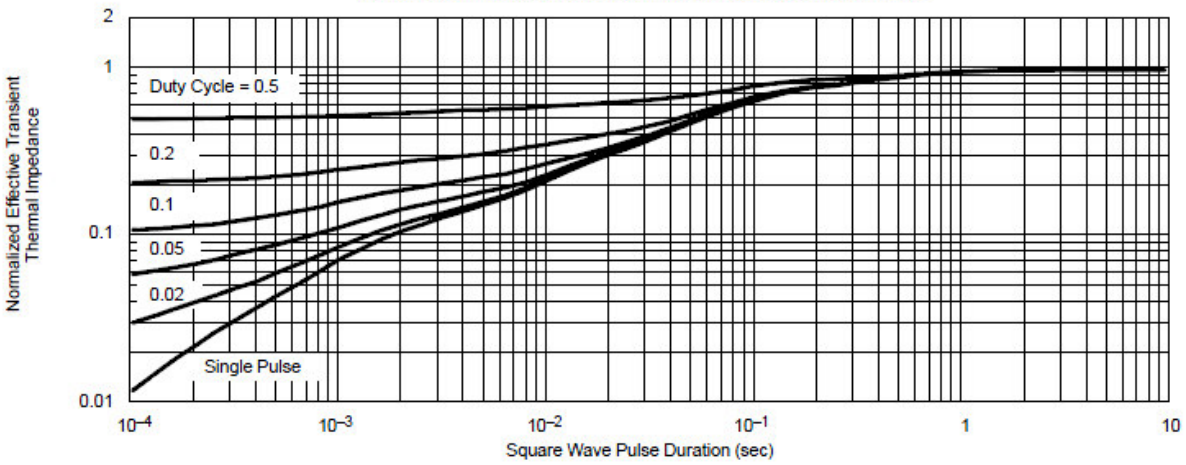
Threshold Voltage



Single Pulse Power

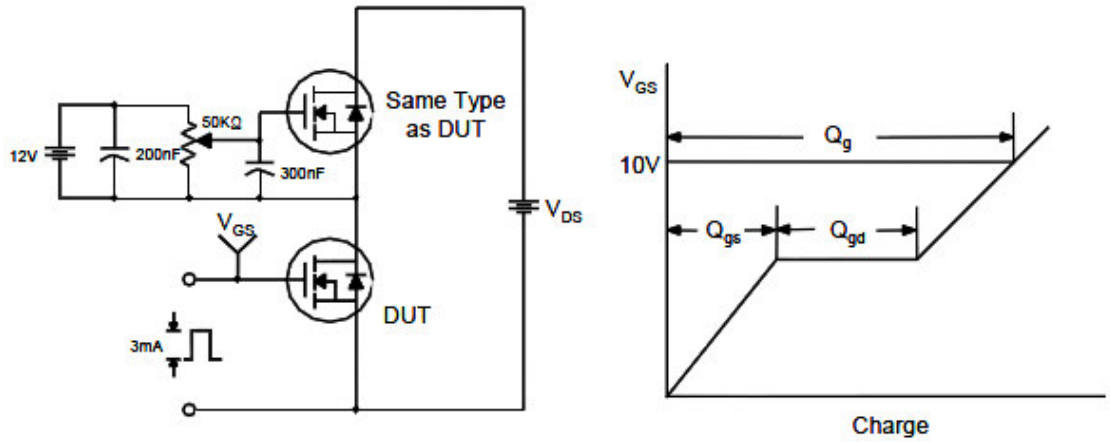


Normalized Thermal Transient Impedance, Junction-to-Foot

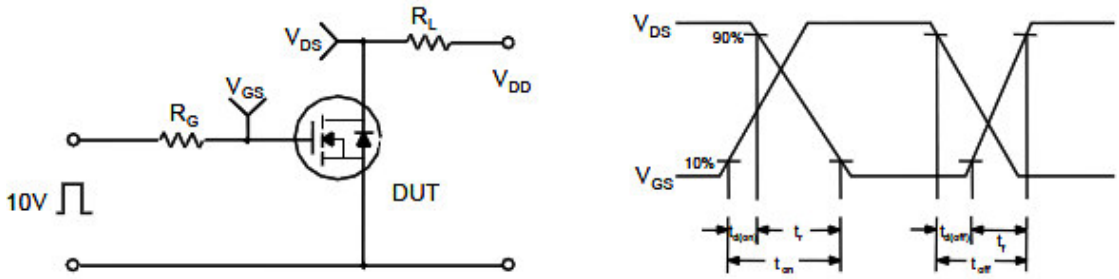


Typical Characteristics

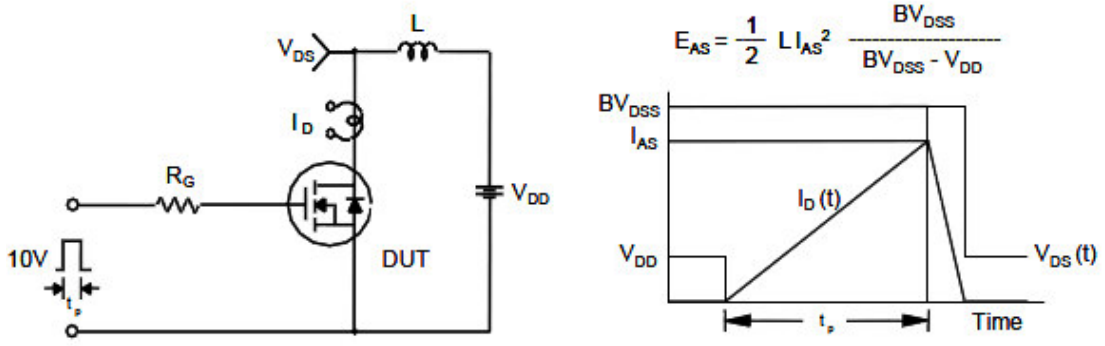
Gate Charge Test Circuit & Waveform



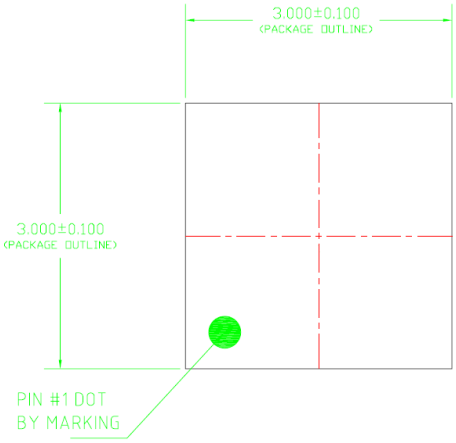
Resistive Switching Test Circuit & Waveforms



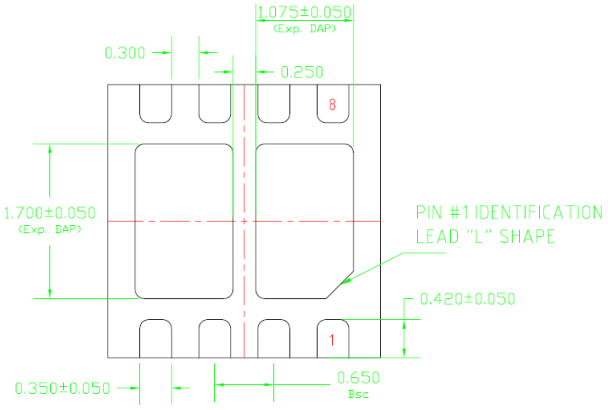
Unclamped Inductive Switching Test Circuit & Waveforms



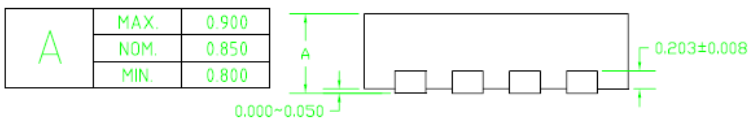
Package Information (DFN3X3-8L)



TOP VIEW



BOTTOM VIEW



SIDE VIEW

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